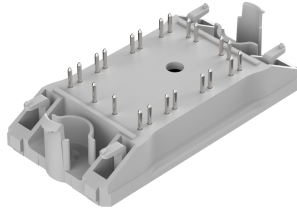
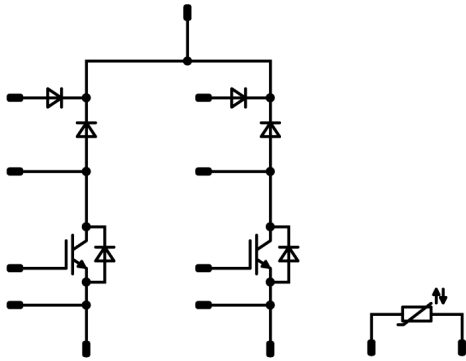




<i>flowBOOST 0 dual</i>		650 V / 50 A
Features	<ul style="list-style-type: none">• High efficiency dual boost• Ultra fast switching frequency• Low Inductance Layout• 650V IGBT and 650V Stealth Si boost diode• Antiparallel IGBT protection diode with high current	flow 0 12 mm housing 
Target applications	<ul style="list-style-type: none">• solar inverter	Schematic 
Types	<ul style="list-style-type: none">• V23990-P623-L82-PM	



Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
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Boost Switch

Collector-emitter voltage	V_{CES}		650	V
Collector current (DC current)	I_C	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	43	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	150	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	84	W
Gate-emitter voltage	V_{GES}		± 20	V
Maximum junction temperature	T_{jmax}		175	°C

Boost Diode

Peak repetitive reverse voltage	V_{RRM}		650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	51	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	88	W
Maximum junction temperature	T_{jmax}		175	°C

Boost Sw. Protection Diode

Peak repetitive reverse voltage	V_{RRM}		650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	21	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	20	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	42	W
Maximum junction temperature	T_{jmax}		175	°C



Vincotech

Maximum Ratings

$T_j = 25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
ByPass Diode				
Peak repetitive reverse voltage	V_{RRM}		1600	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	32	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, $t_p = 10\text{ ms}$ $T_j = 150\text{ °C}$	200	A
Surge current capability	I^2t		200	A ² s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ $T_s = 80\text{ °C}$	42	W
Maximum junction temperature	T_{jmax}		150	°C

Module Properties

Thermal Properties

Storage temperature	T_{stg}		-40...+125	°C
Operation temperature under switching condition	T_{jop}		-40...+($T_{jmax} - 25$)	°C

Isolation Properties

Isolation voltage	V_{isol}	DC Test Voltage* $t_p = 2\text{ s}$	4000	V
Isolation voltage	V_{isol}	AC Voltage $t_p = 1\text{ min}$	2500	V
Creepage distance			>12,7	mm
Clearance			9,55	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production



Vincotech

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Boost Switch

Static

Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = V_{GE}$			0,0005	25	3,3	4	4,7	V
Collector-emitter saturation voltage	$V_{CE(sat)}$		15		50	25 125		1,83 2,01	2,22 ⁽¹⁾	V
Collector-emitter cut-off current	I_{CES}		0	650		25			40	μA
Gate-emitter leakage current	I_{GES}		20	0		25			120	nA
Internal gate resistance	r_g							None		Ω
Input capacitance	C_{ies}							3000		pF
Output capacitance	C_{oes}	$f = 1$ Mhz	0	25		25		50		pF
Reverse transfer capacitance	C_{res}							11		pF
Gate charge	Q_g		15	520	50	25		120		nC

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,13		K/W
--	---------------	---------------------------------------	--	--	--	--	--	------	--	-----

Dynamic

Turn-on delay time	$t_{d(on)}$	$R_{gon} = 8$ Ω $R_{goff} = 8$ Ω	0/15	400	30	25		22,6		ns
						125		21,8		
Rise time	t_r					25		5		
						125		6,8		
Turn-off delay time	$t_{d(off)}$					25		142		
						125		168,4		
Fall time	t_f					25		3,39		ns
						125		6,83		
Turn-on energy (per pulse)	E_{on}	$Q_{tFWD} = 0,477$ μC $Q_{tFWD} = 1,46$ μC				25		0,37		mWs
						125		0,598		
Turn-off energy (per pulse)	E_{off}					25		0,147		mWs
						125		0,285		



Vincotech

V23990-P623-L82-PM
datasheet

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

Boost Diode

Static

Forward voltage	V_F				50	25 125		2,27 1,9	2,6 ⁽¹⁾	V
Reverse leakage current	I_R	$V_r = 650$ V				25			10	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,08		K/W
--	---------------	---------------------------------------	--	--	--	--	--	------	--	-----

Dynamic

Peak recovery current	I_{RRM}	$di/dt=5061$ A/μs $di/dt=3900$ A/μs	0/15	400	30	25		39,89		A
						125		56,1		
Reverse recovery time	t_{rr}					25		18,6		
						125		56,05		
Recovered charge	Q_r					25		0,477		
						125		1,46		
Reverse recovered energy	E_{rec}	25		0,053						
		125		0,281						
Peak rate of fall of recovery current	$(di/dt)_{max}$	25		8359						
		125		3588						

Boost Sw. Protection Diode

Static

Forward voltage	V_F				10	25 125	1,23	1,67 1,54	1,87 ⁽¹⁾	V
Reverse leakage current	I_R	$V_r = 650$ V				25			0,14	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						2,28		K/W
--	---------------	---------------------------------------	--	--	--	--	--	------	--	-----



Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
		V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max		

ByPass Diode

Static

Forward voltage	V_F				8	25 125		0,996 0,901	1,21 ⁽¹⁾ 1,1 ⁽¹⁾	V
Reverse leakage current	I_R	$V_i = 1600$ V				25			50	μA

Thermal

Thermal resistance junction to sink ⁽²⁾	$R_{th(j-s)}$	$\lambda_{paste} = 3,4$ W/mK (PSX)						1,67		K/W
--	---------------	---------------------------------------	--	--	--	--	--	------	--	-----

Thermistor

Static

Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	$R_{100} = 1484$ Ω				100	-5		5	%
Power dissipation	P							5		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

⁽¹⁾ Value at chip level

⁽²⁾ Only valid with pre-applied Vincotech thermal interface material.

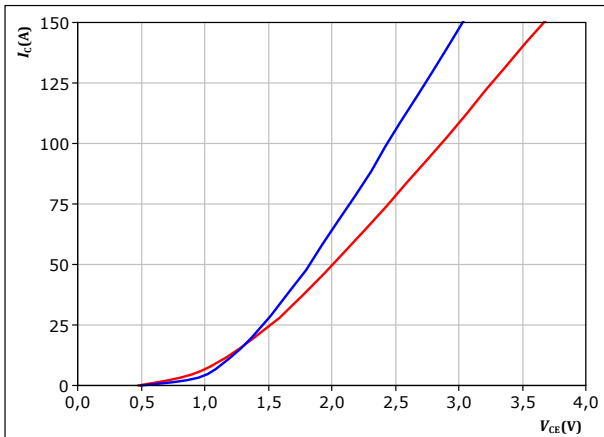


Boost Switch Characteristics

figure 1. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

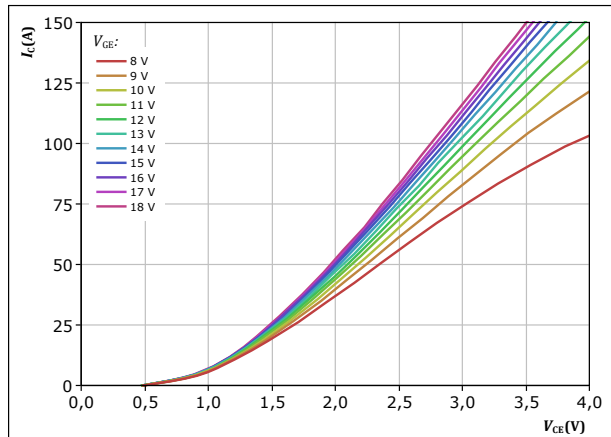


$t_p = 250 \mu\text{s}$
 $V_{GE} = 15 \text{ V}$
 $T_j: 25 \text{ }^\circ\text{C}$ (blue line)
 $125 \text{ }^\circ\text{C}$ (red line)

figure 2. IGBT

Typical output characteristics

$$I_C = f(V_{CE})$$

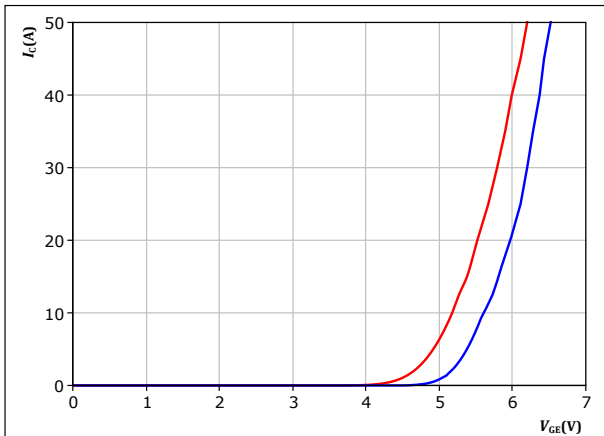


$t_p = 250 \mu\text{s}$
 $T_j = 125 \text{ }^\circ\text{C}$
 V_{GE} from 8 V to 18 V in steps of 1 V

figure 3. IGBT

Typical transfer characteristics

$$I_C = f(V_{GE})$$

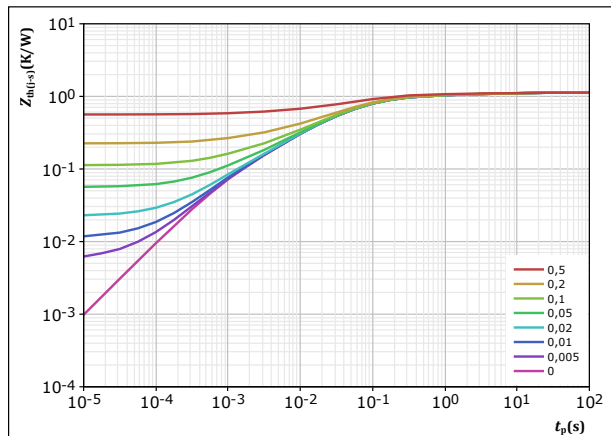


$t_p = 250 \mu\text{s}$
 $V_{CE} = 10 \text{ V}$
 $T_j: 25 \text{ }^\circ\text{C}$ (blue line)
 $125 \text{ }^\circ\text{C}$ (red line)

figure 4. IGBT

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,126 \text{ K/W}$

IGBT thermal model values

R (K/W)	τ (s)
7,12E-02	8,15E+00
1,29E-01	6,00E-01
4,31E-01	9,13E-02
3,15E-01	2,59E-02
1,31E-01	5,80E-03
5,02E-02	8,53E-04

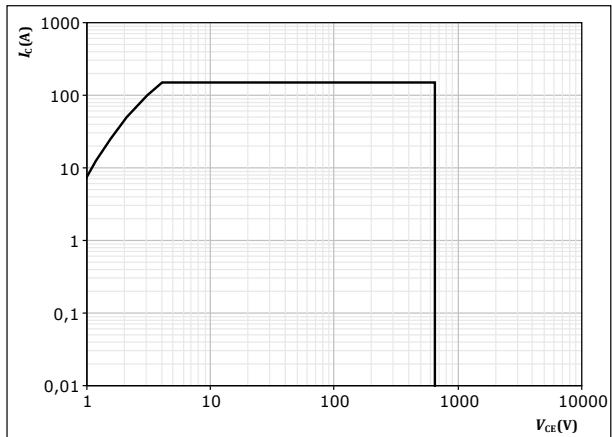


Boost Switch Characteristics

figure 5. IGBT

Safe operating area

$$I_C = f(V_{CE})$$



D = single pulse
T_s = 80 °C
V_{CE} = 15 V
T_j = T_{jmax}



Boost Diode Characteristics

figure 6. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

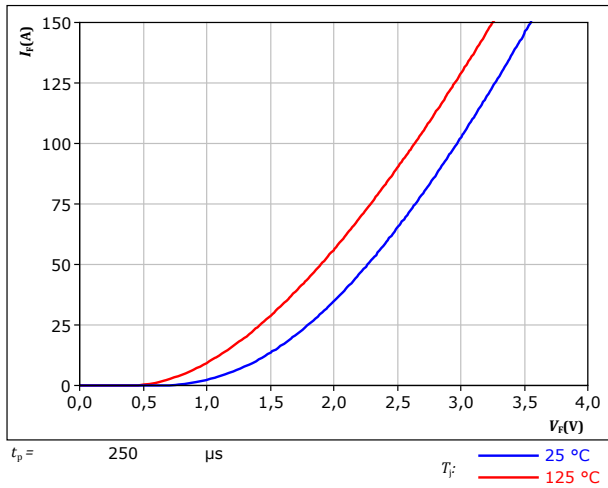
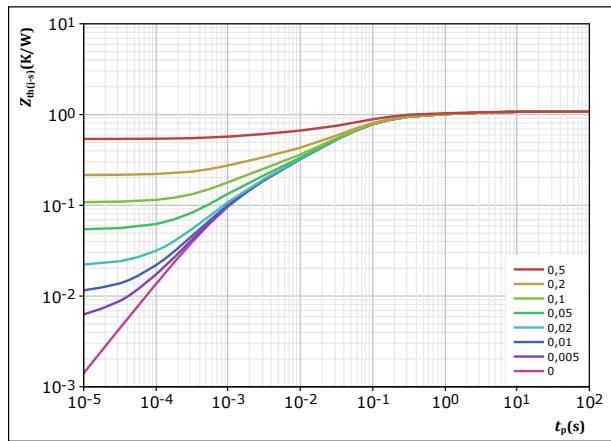


figure 7. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 1,076$ K/W
 FWD thermal model values

R (K/W)	τ (s)
5,58E-02	4,07E+00
1,01E-01	6,75E-01
4,35E-01	9,24E-02
2,93E-01	2,59E-02
1,10E-01	4,04E-03
8,25E-02	8,42E-04

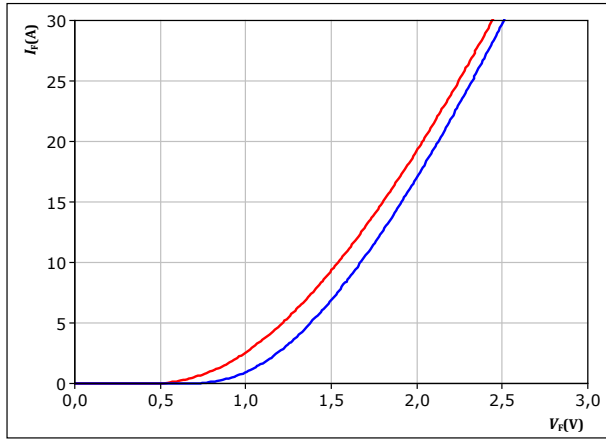


Boost Sw. Protection Diode Characteristics

figure 8. FWD

Typical forward characteristics

$$I_F = f(V_F)$$

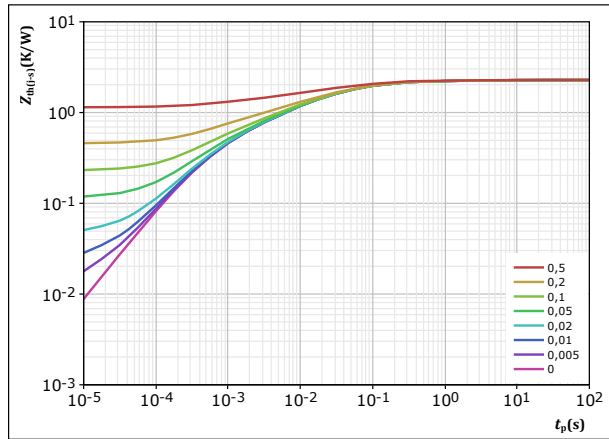


$t_p = 250\text{ }\mu\text{s}$
 T_j : — 25 °C
 — 125 °C

figure 9. FWD

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$
 $R_{th(j-s)} = 2,283\text{ K/W}$
 FWD thermal model values

R (K/W)	τ (s)
4,13E-02	5,13E+00
1,17E-01	6,66E-01
7,33E-01	6,82E-02
6,69E-01	1,26E-02
4,38E-01	2,55E-03
2,85E-01	4,36E-04



ByPass Diode Characteristics

figure 10. Rectifier

Typical forward characteristics

$$I_F = f(V_F)$$

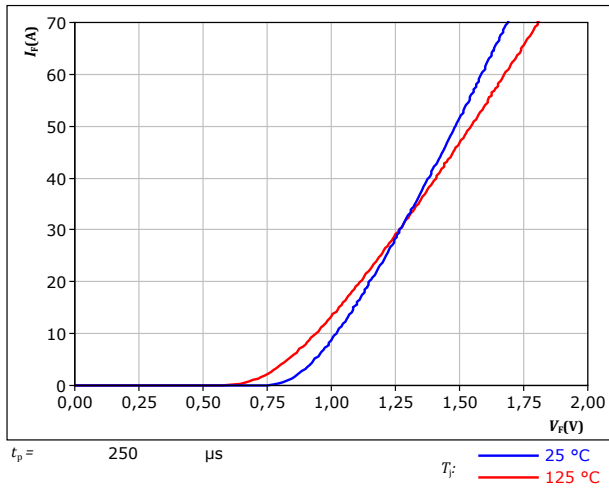
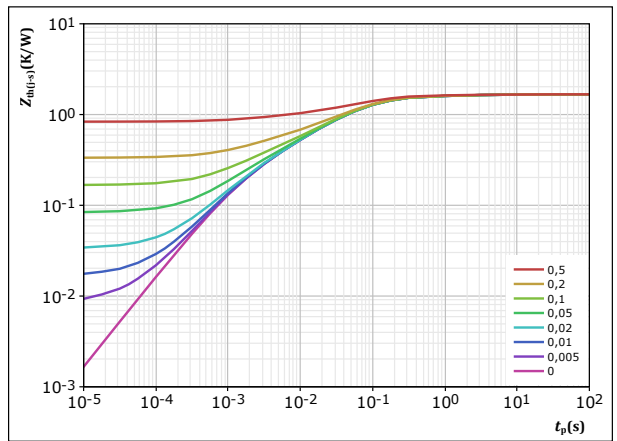


figure 11. Rectifier

Transient thermal impedance as a function of pulse width

$$Z_{th(j-s)} = f(t_p)$$



$D = t_p / T$

$R_{th(j-s)} = 1,67 \text{ K/W}$

Rectifier thermal model values

$R \text{ (K/W)}$	$\tau \text{ (s)}$
3,87E-02	8,07E+00
9,51E-02	9,56E-01
5,99E-01	1,10E-01
5,64E-01	3,17E-02
2,35E-01	6,74E-03
1,38E-01	1,28E-03

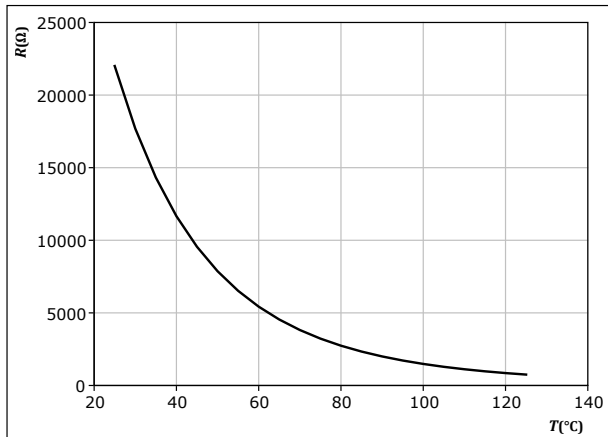


Thermistor Characteristics

figure 12. Thermistor

Typical NTC characteristic as function of temperature

$$R_T = f(T)$$



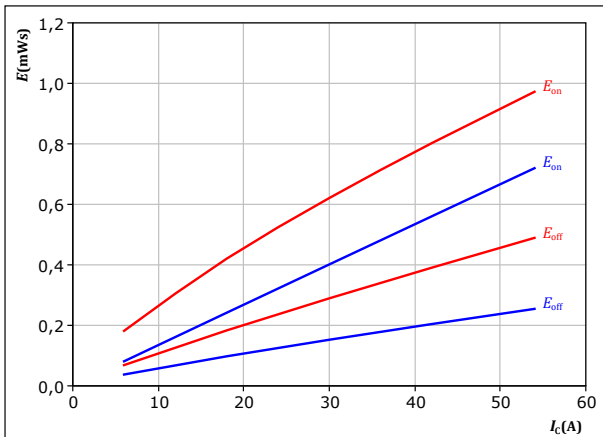


Boost Switching Characteristics

figure 13. IGBT

Typical switching energy losses as a function of collector current

$$E = f(I_c)$$



With an inductive load at

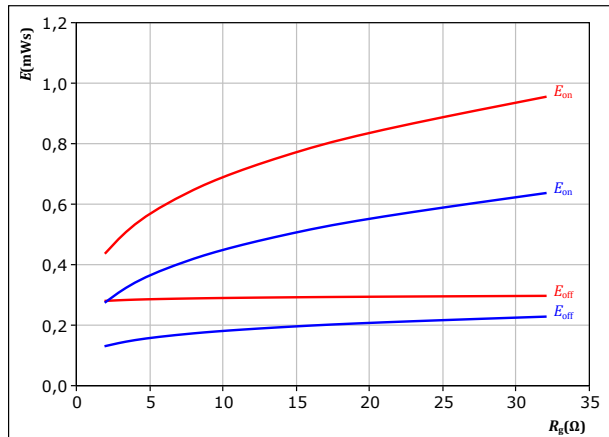
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω
 $R_{goff} = 8$ Ω

T_j : — 25 °C
— 125 °C

figure 14. IGBT

Typical switching energy losses as a function of gate resistor

$$E = f(R_g)$$



With an inductive load at

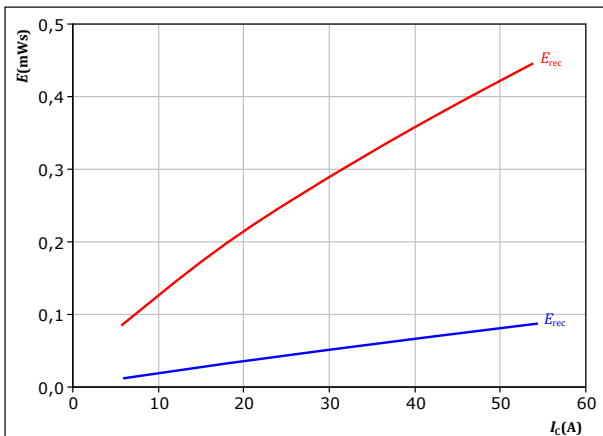
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

T_j : — 25 °C
— 125 °C

figure 15. FWD

Typical reverse recovered energy loss as a function of collector current

$$E_{rec} = f(I_c)$$



With an inductive load at

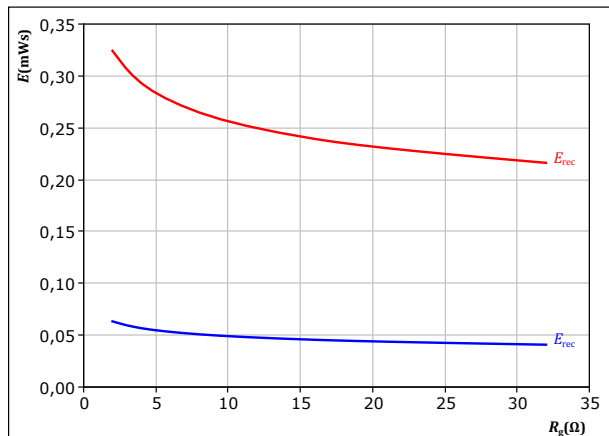
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{gon} = 8$ Ω

T_j : — 25 °C
— 125 °C

figure 16. FWD

Typical reverse recovered energy loss as a function of gate resistor

$$E_{rec} = f(R_g)$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

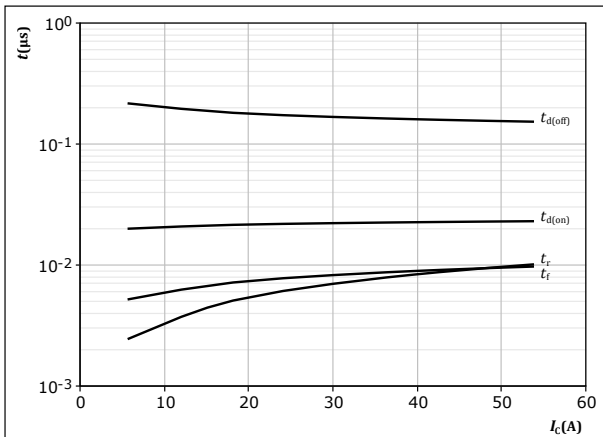
T_j : — 25 °C
— 125 °C



Boost Switching Characteristics

figure 17. IGBT

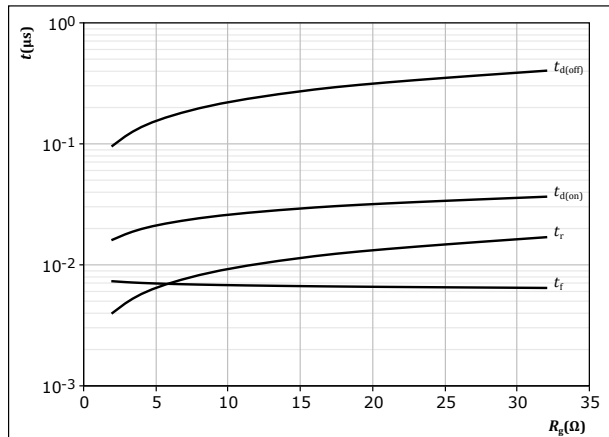
Typical switching times as a function of collector current
 $t = f(I_c)$



With an inductive load at
 $T_j = 125$ °C
 $V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{g(on)} = 8$ Ω
 $R_{g(off)} = 8$ Ω

figure 18. IGBT

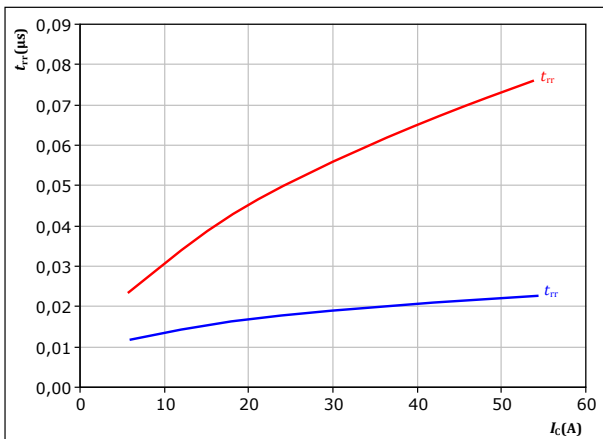
Typical switching times as a function of gate resistor
 $t = f(R_g)$



With an inductive load at
 $T_j = 125$ °C
 $V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

figure 19. FWD

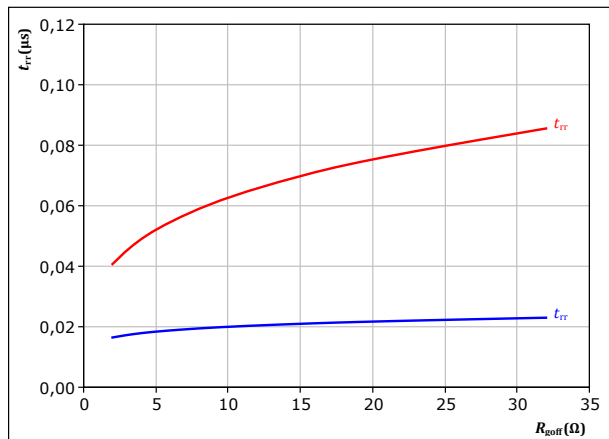
Typical reverse recovery time as a function of collector current
 $t_{rr} = f(I_c)$



With an inductive load at
 $V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{g(on)} = 8$ Ω
 T_j : — 25 °C
— 125 °C

figure 20. FWD

Typical reverse recovery time as a function of IGBT turn off gate resistor
 $t_{rr} = f(R_{g(off)})$



With an inductive load at
 $V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A
 T_j : — 25 °C
— 125 °C

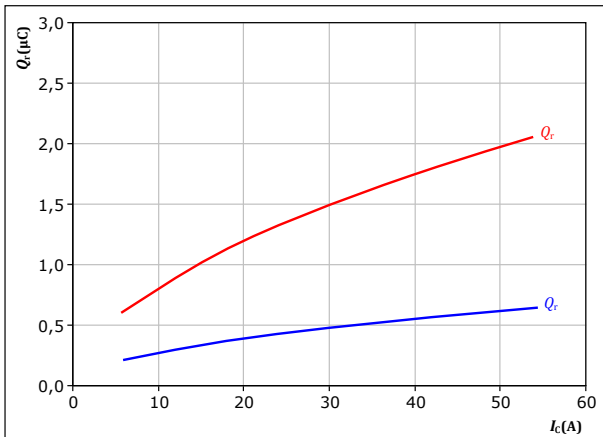


Boost Switching Characteristics

figure 21. FWD

Typical recovered charge as a function of collector current

$$Q_r = f(I_c)$$



With an inductive load at

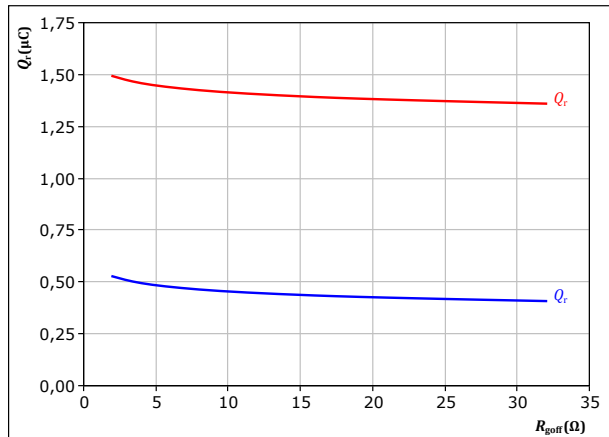
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{goff} = 8$ Ω

T_j : — 25 °C
— 125 °C

figure 22. FWD

Typical recovered charge as a function of turn off gate resistor

$$Q_r = f(R_{goff})$$



With an inductive load at

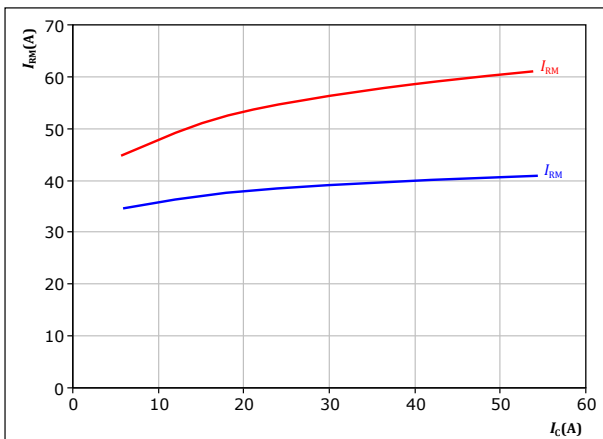
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

T_j : — 25 °C
— 125 °C

figure 23. FWD

Typical peak reverse recovery current as a function of collector current

$$I_{RM} = f(I_c)$$



With an inductive load at

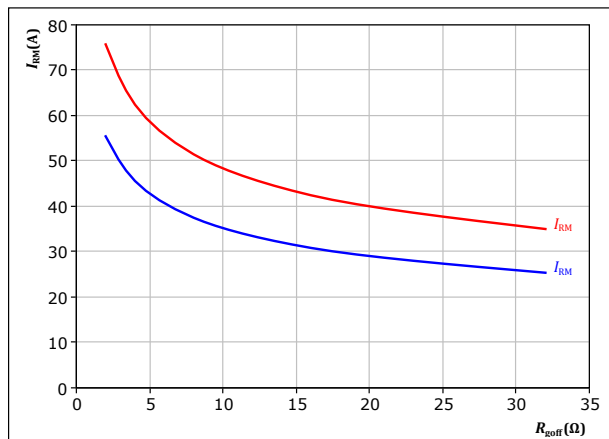
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{goff} = 8$ Ω

T_j : — 25 °C
— 125 °C

figure 24. FWD

Typical peak reverse recovery current as a function of turn off gate resistor

$$I_{RM} = f(R_{goff})$$



With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

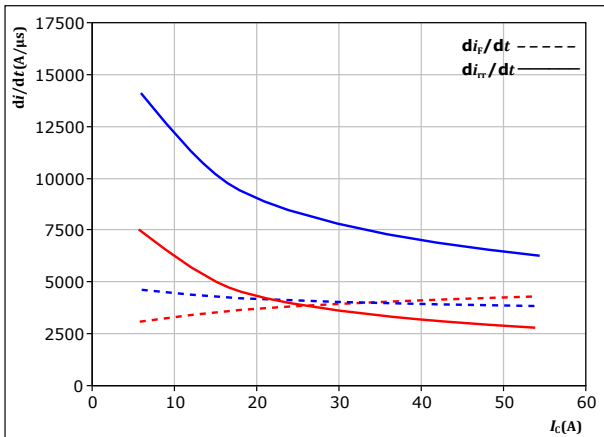
T_j : — 25 °C
— 125 °C



Boost Switching Characteristics

figure 25. FWD

Typical rate of fall of forward and reverse recovery current as a function of collector current
 $di_f/dt, di_r/dt = f(I_c)$



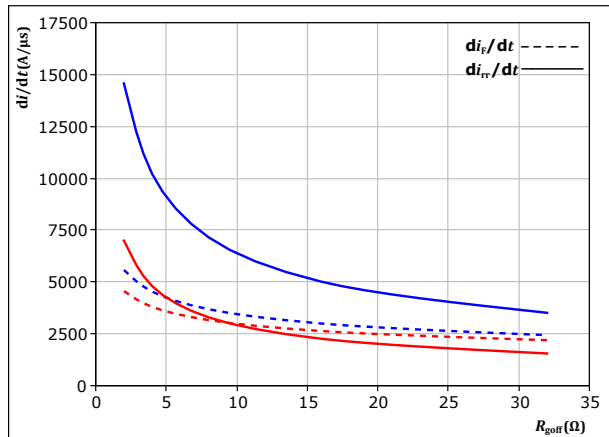
With an inductive load at

$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $R_{g(on)} = 8$ Ω

T_j : — 25 °C
 — 125 °C

figure 26. FWD

Typical rate of fall of forward and reverse recovery current as a function of turn off gate resistor
 $di_f/dt, di_r/dt = f(R_{g(off)})$



With an inductive load at

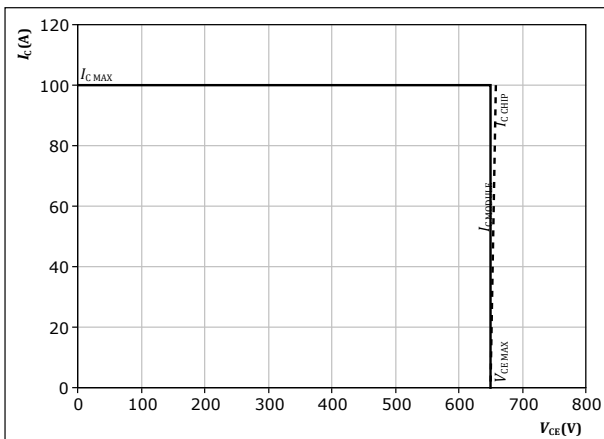
$V_{CE} = 400$ V
 $V_{GE} = 0/15$ V
 $I_c = 30$ A

T_j : — 25 °C
 — 125 °C

figure 27. IGBT

Reverse bias safe operating area

$I_c = f(V_{CE})$



At $T_j = 125$ °C
 $R_{g(on)} = 8$ Ω
 $R_{g(off)} = 8$ Ω



Boost Switching Definitions

figure 28. IGBT

Turn-off Switching Waveforms & definition of t_{doff} , t_{Eoff} (t_{Eoff} = integrating time for E_{off})

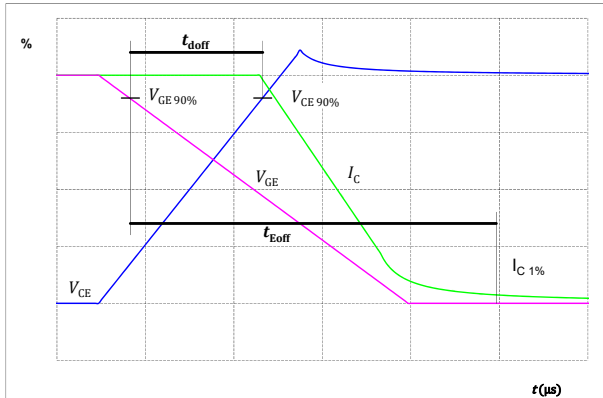


figure 29. IGBT

Turn-on Switching Waveforms & definition of t_{don} , t_{Eon} (t_{Eon} = integrating time for E_{on})



figure 30. IGBT

Turn-off Switching Waveforms & definition of t_f

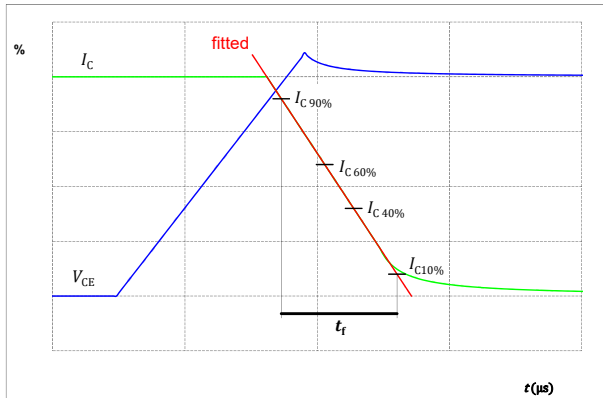
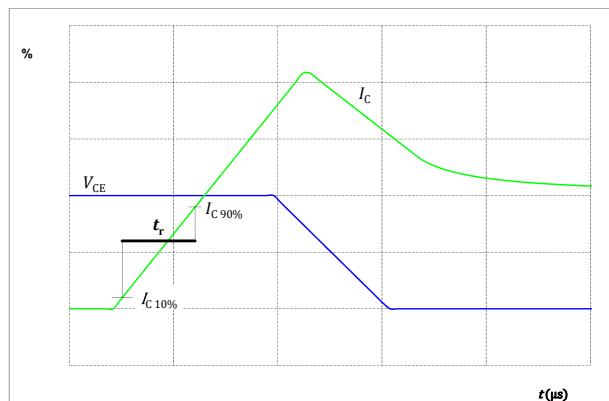


figure 31. IGBT

Turn-on Switching Waveforms & definition of t_r





Boost Switching Definitions

figure 32. FWD

Turn-off Switching Waveforms & definition of t_{rr}

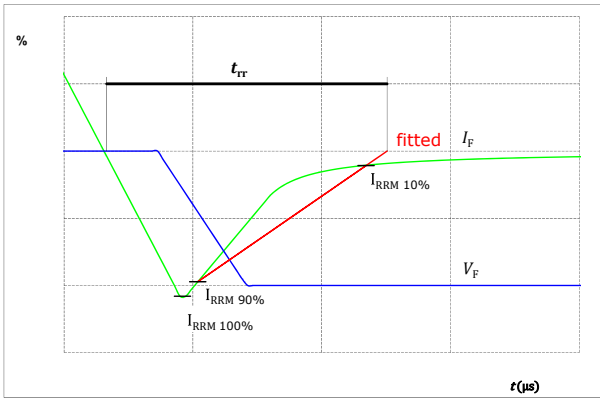
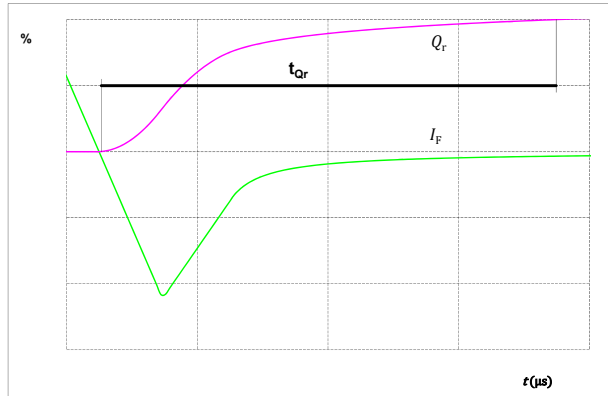


figure 33. FWD

Turn-on Switching Waveforms & definition of t_{Qr} (t_{Qr} = integrating time for Q_r)





Vincotech

V23990-P623-L82-PM
datasheet

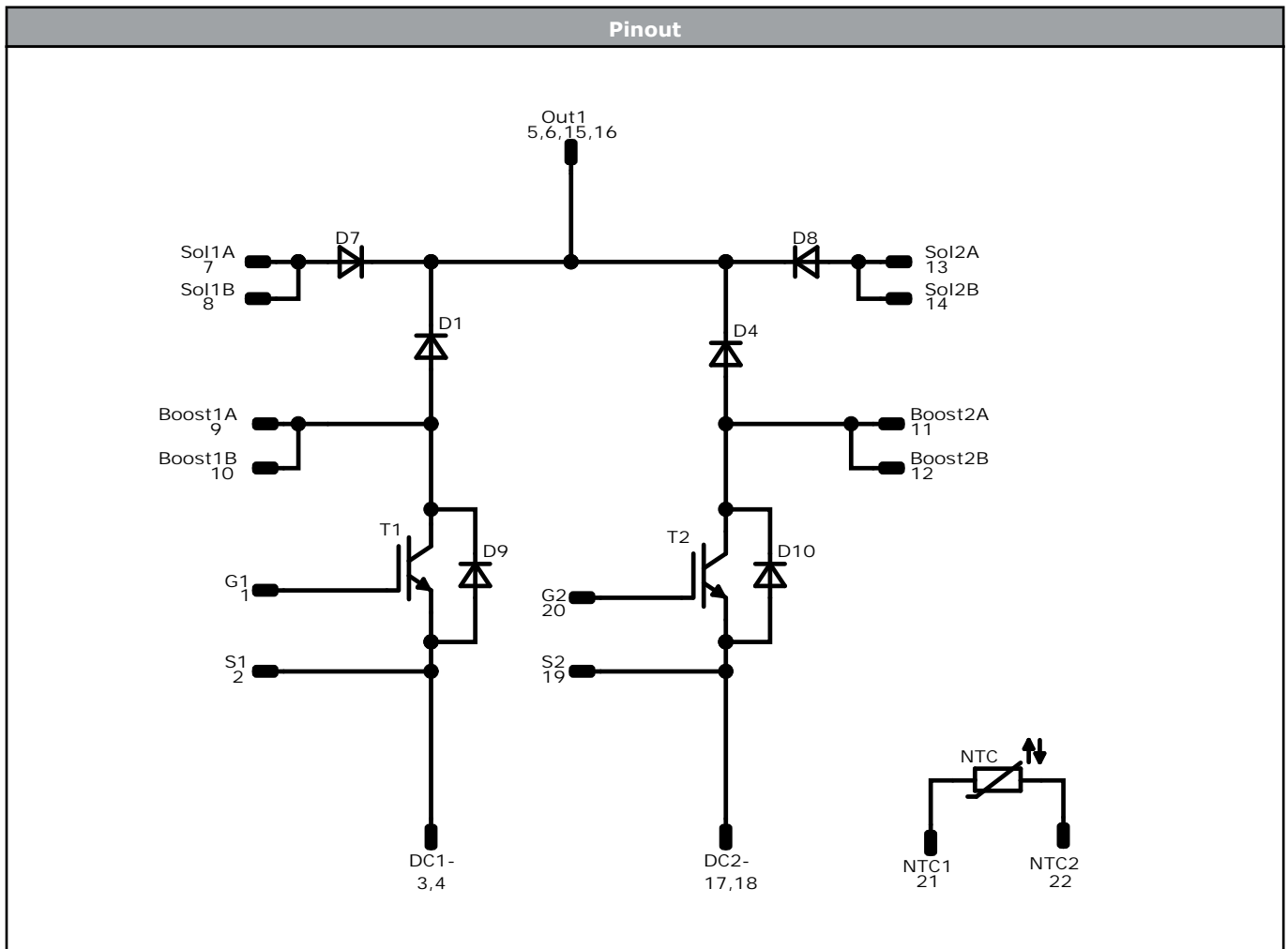
Ordering Code	
Version	Ordering Code
Without thermal paste	V23990-P623-L82-PM
With thermal paste (5,2 W/mK, PTM6000HV)	V23990-P623-L82-7/-PM
With thermal paste (3,4 W/mK, PSX-P7)	V23990-P623-L82-3/-PM

Marking							
	Text	VIN	Date code	Type&Ver	UL	Lot	Serial
		VIN	WWYY	TTTTTTVV	UL	LLLLL	SSSS
	Datamatrix	Type&Ver	Lot number	Serial	Date code		
		TTTTTTVV	LLLLL	SSSS	WWYY		

Pin table [mm]			
Pin	X	Y	Function
1	0	22,5	G1
2	2,9	22,5	S1
3	8,3	22,5	DC1-
4	10,8	22,5	DC1-
5	19,6	22,5	Out1
6	22,1	22,5	Out1
7	29,1	22,5	Sol1A
8	32	22,5	Sol1B
9	33,5	17,8	Boost1A
10	33,5	15,3	Boost1B
11	33,5	7,2	Boost2A
12	33,5	4,7	Boost2B
13	32	0	Sol2A
14	29,1	0	Sol2B
15	22,1	0	Out1
16	19,6	0	Out1
17	10,8	0	DC2-
18	8,3	0	DC2-
19	2,9	0	S2
20	0	0	G2
21	0	8	NTC1
22	0	14,5	NTC2

$\phi 1.40 \pm 0.05$
 16.3 ± 0.05
 11.25
 16.75

Tolerance of pinpositions: ± 0.5 mm at the end of pins
Dimension of coordinate axis is only offset without tolerance



Identification					
ID	Component	Voltage	Current	Function	Comment
T1, T2	IGBT	650 V	50 A	Boost Switch	
D1, D4	FWD	650 V	50 A	Boost Diode	
D9, D10	FWD	650 V	10 A	Boost Sw. Protection Diode	
D7, D8	Rectifier	1600 V	25 A	ByPass Diode	
NTC	Thermistor			Thermistor	




Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for <i>flow 0</i> packages see vincotech.com website.

Package data
Package data for <i>flow 0</i> packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website. 

Document No.:	Date:	Modification:	Pages
V23990-P623-L82-PM-D3-14	12 Sep. 2021	New Datasheet format, module is unchanged	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.